

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	0	((first) near2 transistor) same (second near2 transistor) same ((floating adj gate) near2 transistor) same ((first or second or third) near heavily near (dope or doped)) same conductivity).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:37
S2	0	((first) near2 transistor) same (second near2 transistor) same ((floating adj gate) near2 transistor) same ((first or second or third) near heavily near (dope or doped)) same conductivity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:37
S3	468	((first) near2 transistor) same (second near2 transistor) same ((floating adj gate) near2 transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:37
S4	204	((first) near2 transistor) same (second near2 transistor) same ((floating adj gate) near2 transistor)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:37
S5	1	((first) near2 transistor) same (second near2 transistor) same ((floating adj gate) near2 transistor) same (esd or electrostatic)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:38
S6	4	((first) near2 transistor) same (second near2 transistor) same ((floating adj gate) near2 transistor)) and (esd or electrostatic)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:39
S7	6	((first) near2 transistor) same (second near2 transistor) same ((floating adj gate))) and (esd or electrostatic)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:41
S8	376	((first) near2 transistor) same (second near2 transistor) same ((floating adj gate))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:41
S9	295	((first) near2 transistor) with (second near2 transistor) with ((floating adj gate))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:41

S10	312	((first) near2 (mos of mosfet or transistor)) with (second near2 (mos or mosfet or transistor)) with ((floating adj gate))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:42
S11	6	((first) near2 (mos of mosfet or transistor)) with (second near2 (mos or mosfet or transistor)) with ((floating adj gate))).clm. and (esd or electrostatic).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:44
S12	6	((first) near3 (mos of mosfet or transistor)) with (second near3 (mos or mosfet or transistor)) with ((floating adj gate) near3 transistor)).clm. and (esd or electrostatic).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:47
S13	17121	"257" and (esd or electrostatic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:47
S14	409	"257" and (esd or electrostatic) and (floating adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:53
S15	197	"257" and (esd or electrostatic) and (floating adj gate).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:48
S16	62	"257" and (esd or electrostatic).ti, ab,clm. and (floating adj gate).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:51
S17	32	"257" and (esd or electrostatic).ti, ab,clm. and (floating adj gate).ti, ab,clm. and (dope or doped or doping or conductivity or impurity).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:49
S18	46	S14 and chen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:53

S19	64	(US-20040041215-\$ or US-20040004231-\$ or US-20020195648-\$ or US-20020005544-\$ or US-20010039091-\$ or US-20020140023-\$ or US-20020014656-\$).did. or (US-6809386-\$ or US-5589699-\$ or US-5519240-\$ or US-4495427-\$ or US-6826128-\$ or US-6008508-\$ or US-6670679-\$ or US-6610262-\$ or US-6560080-\$ or US-6448593-\$ or US-6388922-\$ or US-6373095-\$ or US-6265251-\$ or US-6239465-\$ or US-6055143-\$ or US-5986308-\$ or US-5932916-\$ or US-5909347-\$ or US-5869873-\$ or US-5844300-\$ or US-5838033-\$ or US-5272586-\$ or US-5195010-\$ or US-4087795-\$ or US-3590343-\$ or US-6825525-\$).did. or (US-6680505-\$ or US-6597048-\$ or US-6556025-\$ or US-6426529-\$ or US-6175394-\$ or US-6133601-\$ or US-5986939-\$ or US-5506159-\$ or US-6034552-\$).did. or (JP-05343696-\$ or JP-04324980-\$ or JP-61230376-\$ or JP-61131486-\$ or JP-60115266-\$ or JP-06053463-\$ or JP-05090610-\$ or JP-63202062-\$ or JP-62123773-\$ or JP-62020376-\$ or JP-61240675-\$ or JP-61193484-\$ or JP-61184883-\$ or JP-60232788-\$ or JP-60147128-\$ or JP-58158973-\$ or JP-58114459-\$ or JP-57039583-\$ or JP-56090564-\$ or JP-56076559-\$ or JP-55118678-\$ or JP-53059381-\$).did.	US-PGPUB; USPAT; JPO	OR	ON	2004/12/09 12:58
S20	23	S19 and ((floating adj gate) near3 (mos of mosfet or transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:58
S21	20	S19 and ((floating adj gate) near3 (mos of mosfet or transistor)).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:59

S22	12	S19 and ((floating adj gate) near3 (mos of mosfet or transistor)).ti, ab,clm. and ((first or second or third) near3 (transistor or mosfet or mos)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 12:59
S23	13	S19 and ((floating adj gate) near3 (mos of mosfet or transistor)).ti, ab,clm. and ((first or second or third) near5 (transistor or mosfet or mos)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:00
S24	14	S19 and ((floating adj gate) near5 (mos of mosfet or transistor)).ti, ab,clm. and ((first or second or third) near5 (transistor or mosfet or mos)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:00
S25	11	S19 and ((floating adj gate) near5 (mos of mosfet or transistor)).ti, ab,clm. with ((first or second or third) near5 (transistor or mosfet or mos)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:01
S26	9	S19 and ((floating adj gate) near5 (mos of mosfet or transistor)).ti, ab,clm. with ((first or second or third) near5 (transistor or mosfet or mos) with (dope or doped or doping or impurity or region or conductivity)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:03
S27	0	S19 and ((floating adj gate) near5 (mos of mosfet or transistor)).ti, ab,clm. with ((first or second or third) near5 (transistor or mosfet or mos) with ((n+ or p+ or heavy or heavily) near5 (dope or doped or doping or impurity or region or conductivity))).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:05
S28	13	((floating adj gate) near5 (mos of mosfet or transistor)).ti,ab,clm. with ((first or second or third) near5 (transistor or mosfet or mos) with ((n+ or p+ or heavy or heavily) near5 (dope or doped or doping or impurity or region or conductivity))).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:05
S29	14	((floating adj gate) near5 (mos of mosfet or transistor)).ti,ab,clm. with ((first or second or third) near5 (transistor or mosfet or mos) with ((idd or hdd or n+ or p+ or heavy or heavily) near5 (dope or doped or doping or impurity or region or conductivity))).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:07

S30	0	((floating adj gate) near5 (mos of mosfet or transistor)).ti,ab,clm. with ((first or second or third) near5 (transistor or mosfet or mos) with ((ldd or hdd or n+ or p+ or heavy or heavily) near5 (dope or doped or doping or impurity or region or conductivity))) and (esd or electrostatic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:10
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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S32	1	((floating adj gate) near5 (mos of mosfet or transistor)).ti,ab,clm. with ((first or second or third) near5 (transistor or mosfet or mos) with (((ldd or hdd or n+ or p+ or heavy or heavily) near5 (dope or doped or doping or impurity or region or conductivity)))) or (n+ or p+ or hdd or ldd)) and (esd or electrostatic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:12
S33	145	(floating adj gate).ti,ab,clm. and (esd or electrostatic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:13
S34	44	((transistor or mosfet or mos) near5 (floating adj gate)).ti,ab,clm. and (esd or electrostatic).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:13

S35	86	(US-20040041215-\$ or US-20040004231-\$ or US-20020195648-\$ or US-20020005544-\$ or US-20010039091-\$ or US-20020140023-\$ or US-20020014656-\$).did. or (US-6809386-\$ or US-5589699-\$ or US-5519240-\$ or US-4495427-\$ or US-6826128-\$ or US-6008508-\$ or US-6670679-\$ or US-6610262-\$ or US-6560080-\$ or US-6448593-\$ or US-6388922-\$ or US-6373095-\$ or US-6265251-\$ or US-6239465-\$ or US-6055143-\$ or US-5986308-\$ or US-5932916-\$ or US-5909347-\$ or US-5869873-\$ or US-5844300-\$ or US-5838033-\$ or US-5272586-\$ or US-5195010-\$ or US-4087795-\$ or US-3590343-\$ or US-6825525-\$).did. or (US-6680505-\$ or US-6597048-\$ or US-6556025-\$ or US-6426529-\$ or US-6175394-\$ or US-6133601-\$ or US-5986939-\$ or US-5506159-\$ or US-6034552-\$ or US-6829200-\$ or US-6014305-\$ or US-5661686-\$ or US-5243490-\$).did. or (EP-497471-\$).did. or (JP-05343696-\$ or JP-04324980-\$ or JP-61230376-\$ or JP-61131486-\$ or JP-60115266-\$ or JP-06053463-\$ or JP-05090610-\$ or JP-63202062-\$ or JP-62123773-\$ or JP-62020376-\$ or JP-61240675-\$ or JP-61193484-\$ or JP-61184883-\$ or JP-60232788-\$ or JP-60147128-\$ or JP-58158973-\$ or JP-58114459-\$ or JP-57039583-\$ or JP-56090564-\$ or JP-56076559-\$ or JP-55118678-\$ or JP-53059381-\$ or JP-2003007833-\$ or JP-07254299-\$ or JP-03174679-\$ or JP-02035639-\$).did. or (JP-62023685-\$).did. or (WO-2004090195-\$ or US-6556025-\$ or KR-2003001809-\$ or US-20020195648-\$ or TW-507356-\$ or US-6448593-\$ or JP-11297861-\$ or FR-2772989-\$ or US-5844300-\$ or US-5519240-\$ or EP-497471-\$ or DE-3121494-\$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/09 13:15
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S36	27	S35 and (p+ or n+ or ldd or hdd or ((heavily or heavy) near2 (dope or doped or doping)) or impurity or conductivity).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:18
S37	27	S35 and (p+ or n+ or ldd or hdd or ((heavily or heavy) near2 (dope or doped or doping)) or impurity or conductivity).ti,ab,clm. and (floating adj gate).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:18
S38	5144	(p+ or n+ or ldd or hdd or ((heavily or heavy) near2 (dope or doped or doping)) or impurity or conductivity).ti,ab,clm. and (floating adj gate).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:18
S39	27	S35 and (p+ or n+ or ldd or hdd or ((heavily or heavy) near2 (dope or doped or doping)) or impurity or conductivity).ti,ab,clm. and (floating adj gate).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:20
S40	13	S35 and (p+ or n+ or ldd or hdd or ((heavily or heavy) near2 (dope or doped or doping)) or impurity or conductivity).ti,ab,clm. and ((transistor or mosfet or mos) near5 (floating adj gate)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:22
S41	12	S35 and (p+ or n+ or ldd or hdd or ((heavily or heavy) near2 (dope or doped or doping)) or impurity or conductivity).clm. and ((transistor or mosfet or mos) near5 (floating adj gate)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:22
S42	11	S35 and (p+ or n+ or ldd or hdd or ((heavily or heavy) near2 (dope or doped or doping)) or impurity or conductivity).clm. and ((transistor or mosfet or mos) near5 (floating adj gate)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 13:24

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	16	(floating near2 gate near2 transistor).clm. and (esd or electrostatic).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:28